

In the Claims:

Please cancel claims 1 and 6 without prejudice or disclaimer.

Please amend claims 2-3 and 7-8, as follows:

Claim 1 (currently canceled)

Claim 2 (currently amended) The ~~gate structure~~ method according to claim 4 ~~3~~, wherein the etching prevention layer is titanium or titanium nitride.

Claim 3 (currently amended) A method for forming a gate electrode of high integration semiconductor device comprising the steps of:

sequentially depositing a gate oxide layer, a polysilicon layer, a tungsten nitride layer, a tungsten layer, and a nitride layer on the semiconductor substrate to form a resultant ~~material~~ structure on the semiconductor substrate;

depositing an etching prevention layer on the resultant structure; and  
depositing an anti-reflection layer sequentially on the etching prevention layer resultant material;

forming a pattern by depositing a photoresist layer on the anti-reflection layer and executing a mask process;

etching the nitride layer, the tungsten layer and the tungsten nitride layer sequentially with an etching gas comprising fluorine; and

etching the etching prevention layer and the polysilicon layer with an etching gas comprising chlorine.

Claim 4 (original) The method for forming a gate according to claim 3, wherein the etching prevention layer has a thickness ranging from about 50 to about 1000Å.

Claim 5 (original) The method for forming a gate according to claim 3, wherein the etching gas comprising fluorine is selected from the group consisting of NF<sub>3</sub>, SF<sub>6</sub> and CF<sub>4</sub> gases.

Claim 6 (currently canceled)

Claim 7 (currently amended) The ~~semiconductor device~~ method of claim 6 8, wherein the etching prevention layer is titanium or titanium nitride

Claim 8 (currently amended) A method for forming a gate electrode of a high integration semiconductor device comprising the steps of:

- providing a semiconductor substrate,
- sequentially depositing a gate oxide layer, a polysilicon layer, a tungsten nitride layer, a tungsten layer and a nitride layer on the semiconductor substrate,
- depositing an etching prevention layer on the nitride layer,
- depositing an anti-reflection layer on the etching prevention layer;
- forming a pattern by depositing a photoresist layer on the anti-reflection layer using a mask process,
- etching the nitride layer, the tungsten layer and the tungsten nitride layer sequentially with an etching gas comprising fluorine, and
- etching the etching prevention layer and the polysilicon layer with an etching gas comprising chlorine.

Claim 9 (original) The method of claim 8, wherein the etching prevention layer has a thickness ranging from about 50 to about 1000 Å.

Claim 10 (original) The method of claim 8, wherein the etching gas comprising fluorine is selected from the group consisting of  $\text{NF}_3$ ,  $\text{SF}_6$  and  $\text{CF}_4$  gases.